

NPN 500 mA, 50 V resistor-equipped transistor; R1 = 1 k Ω , R2 = 10 k Ω

Rev. 02 — 23 March 2009

Product data sheet

1. Product profile

1.1 General description

NPN 500 mA Resistor-Equipped Transistor (RET) in a small Surface-Mounted Device (SMD) plastic package.

PNP complement: PDTB113ZT.

1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- **500 mA output current capability**

1.3 Applications

- Digital application in automotive and industrial segments
- Controlling IC inputs

Reduces component count

- Reduces pick and place costs
- ±10 % resistor ratio tolerance
- Cost-saving alternative for BC817 series in digital applications
- Switching loads

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	50	V
lo	output current		-	-	500	mA
R1	bias resistor 1 (input)		0.7	1	1.3	kΩ
R2/R1	bias resistor ratio		9	10	11	



2. Pinning information

Table 2.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	input (base)		
2	GND (emitter)		3
3	output (collector)		
			sym007

3. Ordering information

Table 3. Ordering information			
Type number Package			
	Name	Description	Version
PDTD113ZT	-	plastic surface-mounted package; 3 leads	SOT23

4. Marking

Table 4. Marking codes	
Type number	Marking code ^[1]
PDTD113ZT	*7V

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong * = t: made in Malaysia
 - * = W: made in China

5. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter	-	50	V
V _{CEO}	collector-emitter voltage	open base	-	50	V
V_{EBO}	emitter-base voltage	open collector	-	5	V
VI	input voltage				
	positive		-	+10	V
	negative		-	-5	V
lo	output current		-	500	mA

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NPN 500 mA resistor-equipped transistor; R1 = 1 k Ω , R2 = 10 k Ω

Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

			,		
Symbol	Parameter	Conditions	Min	Мах	Unit
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> _	250	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	500	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

7. Characteristics

Table 7.Characteristics

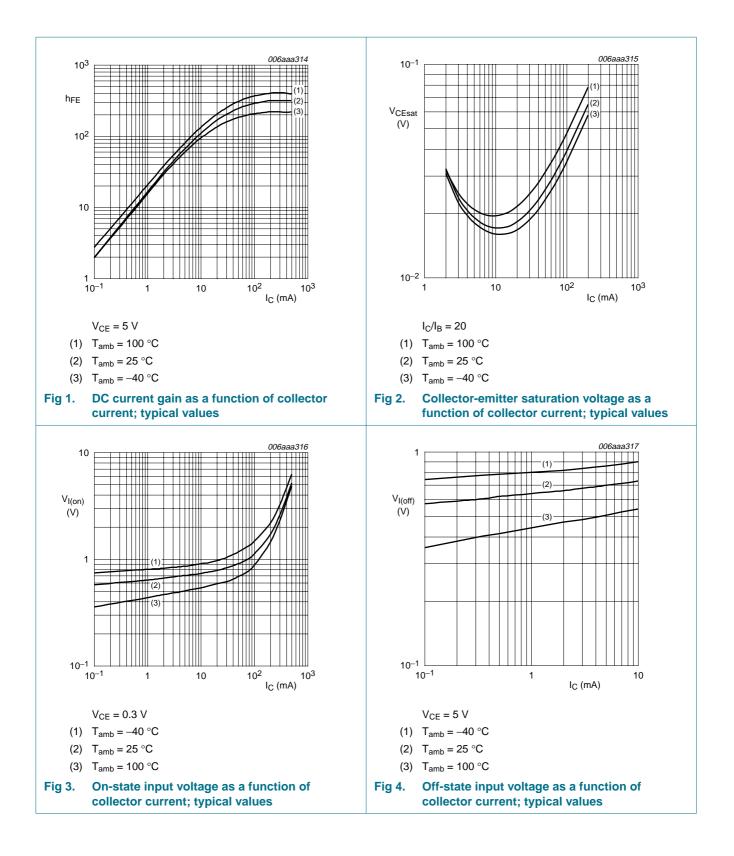
 $T_{amb} = 25 \circ C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	$V_{CB} = 40 \text{ V}; \text{ I}_{E} = 0 \text{ A}$	-	-	100	nA
	current	$V_{CB} = 50 \text{ V}; \text{ I}_{E} = 0 \text{ A}$	-	-	100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = 50 \text{ V}; \text{ I}_{B} = 0 \text{ A}$	-	-	0.5	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 V; I_C = 0 A$	-	-	0.8	mA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 50 \text{ mA}$	70	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = 50 \text{ mA}; I_{B} = 2.5 \text{ mA}$	-	-	0.3	V
V _{I(off)}	off-state input voltage	V_{CE} = 5 V; I_C = 100 μ A	0.3	0.6	1	V
V _{I(on)}	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 20 \text{ mA}$	0.4	0.8	1.4	V
R1	bias resistor 1 (input)		0.7	1	1.3	kΩ
R2/R1	bias resistor ratio		9	10	11	
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 100 MHz	-	7	-	pF

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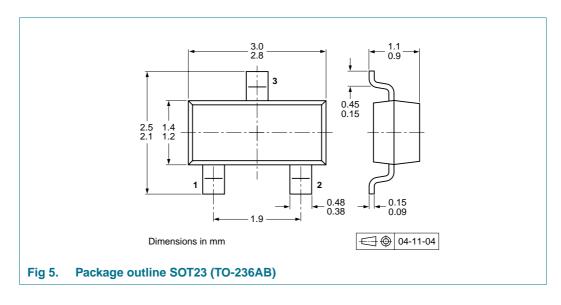
PDTD113ZT

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NPN 500 mA resistor-equipped transistor; R1 = 1 k Ω , R2 = 10 k Ω

8. Package outline



9. Packing information

Table 8. Packing methods

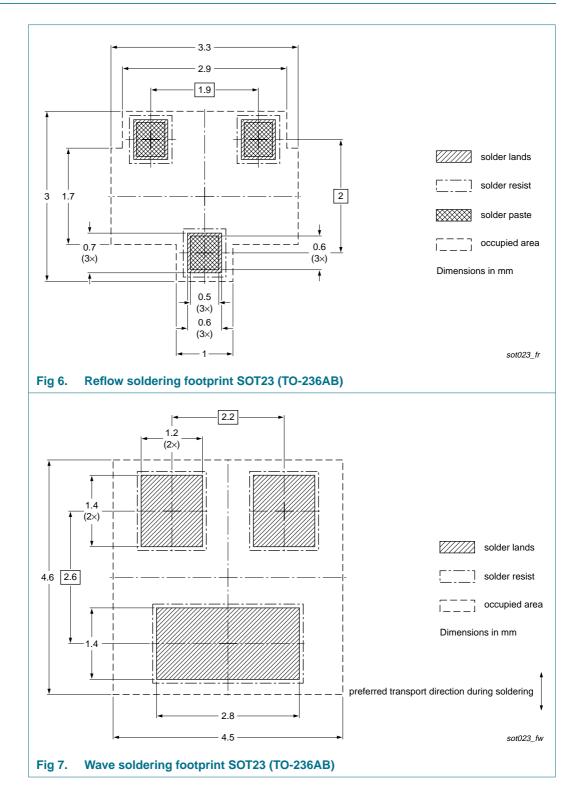
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing	quantity
			3000	10000
PDTD113ZT	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235

[1] For further information and the availability of packing methods, see Section 13.

NPN 500 mA resistor-equipped transistor; R1 = 1 k Ω , R2 = 10 k Ω

10. Soldering



11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
PDTD113ZT_2	20090323	Product data sheet	-	PDTD113Z_SER_1	
Modifications:		f this data sheet has been NXP Semiconductors.	redesigned to comply	with the new identity	
	 Legal texts h 	ave been adapted to the n	ew company name wh	ere appropriate.	
	 Type numbers PDTD113ZK and PDTD113ZS removed 				
	 Table 5 "Limiting values": typo for maximum value of V_I positive corrected 				
	 Section 10 "Soldering": added 				
	 Section 12 "L 	egal information": updated	Ł		
PDTD113Z SER 1	20050405	Product data sheet	-	-	

12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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Date of release: 23 March 2009 Document identifier: PDTD113ZT_2



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NXP: PDTD113ZT,215